

Designed for broadband high power applications, this amplifier utilizes power GaAsFET devices that provide high gain, wide dynamic range, and excellent linearity. Exceptional performance, long term reliability, and high efficiency are achieved by employing advanced broadband RF matching networks and combining techniques, EMI/RFI filters, custom-machined housings, and qualified components. Each unit undergoes extensive burn-in prior to final test and inspection.

ELECTRICAL SPECIFICATIONS @ T=25°C, VDD=+13VDC

Characteristics	Rating	Limit
Frequency Response	800 – 3000 MHz	Min
Power Output CW	10 Watts	Min
Power Output @ 1 dB comp.	8 Watts	Min
Small Signal Gain	40 dB	Min
Small Signal Gain Flatness	±1.5 dB	Max
Third Order Intercept Point	+48 dBm	Typ
Input Overdrive	+10 dBm	Max
Input/Output VSWR @ 50 ohm	2:1	Max
Harmonics @ 1 dB compression	-20 dBc	Typ
Noise Figure	10 dB	Max
Spurious Signals	-60 dBc	Max
Supply Voltage	+12 to +15VDC	Nom
Current Consumption	5 Amp	Max

ENVIRONMENTAL CHARACTERISTICS

Operating Temperature: 0°C to +50°C

Non-operating Temperature: -40°C to +85°C

Humidity: 95% relative without condensation

Altitude: 10,000 feet

Shock and Vibration: Normal truck transport

CIRCUIT PROTECTIONS

Infinite Load VSWR

RF Input Overdrive

MECHANICAL SPECIFICATIONS

Dimensions	TBD	Max
Weight	1.5 lb.	Max
RF Connectors	SMA female	
Cooling	External Heatsink	

